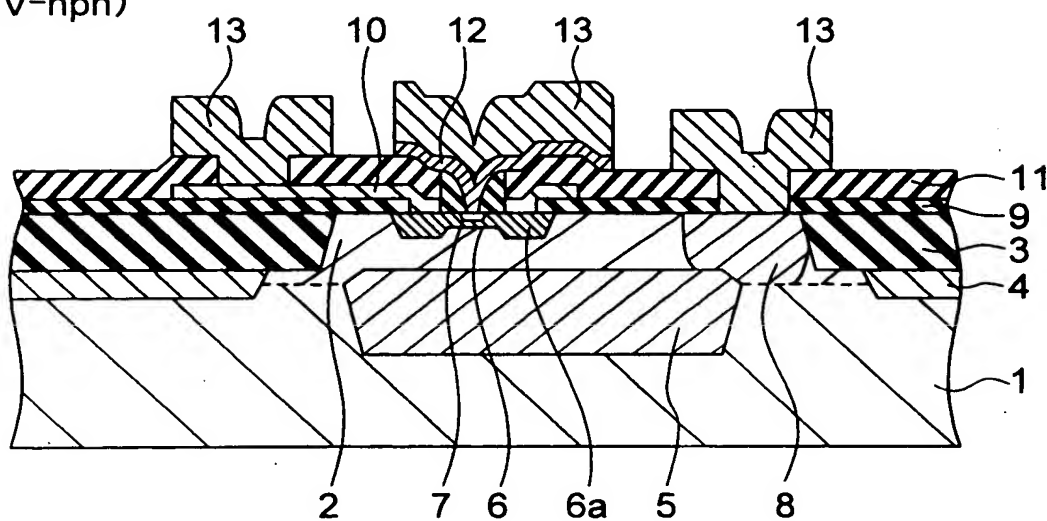


(V-npn)





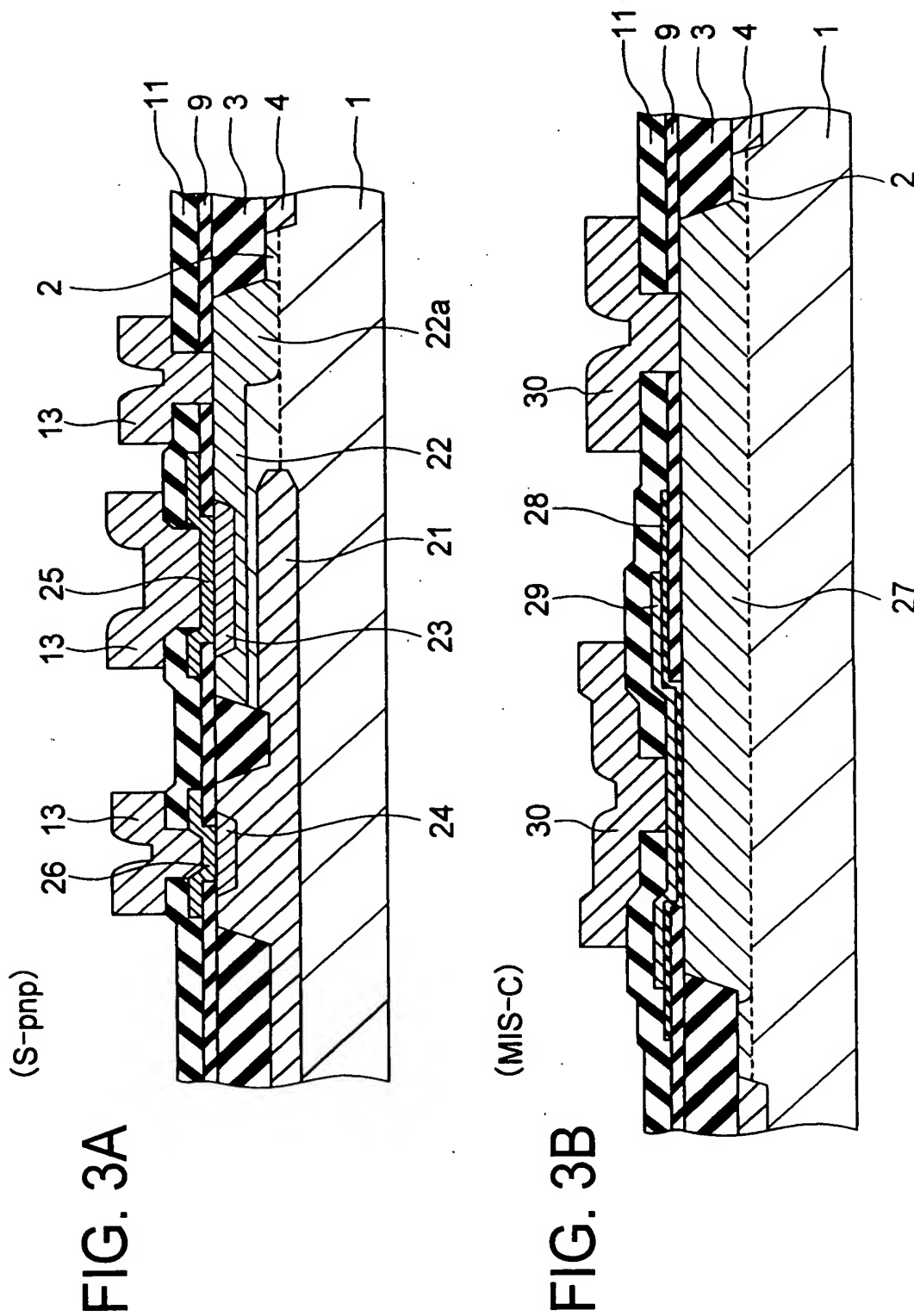
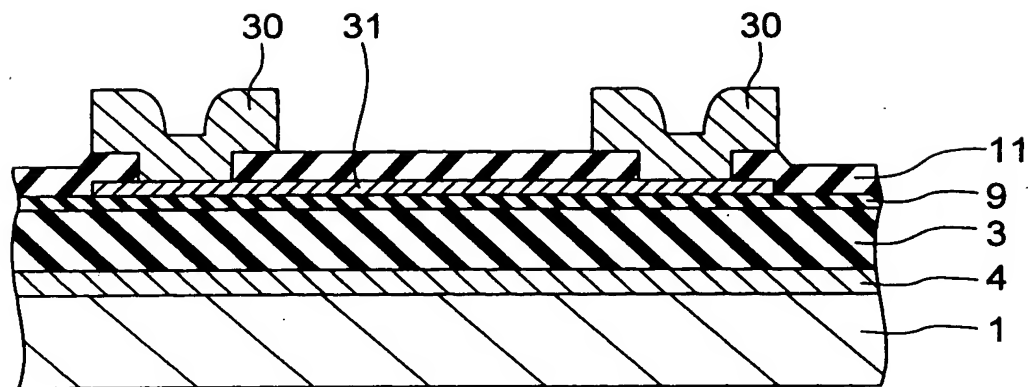


FIG. 4

(Poly-R)



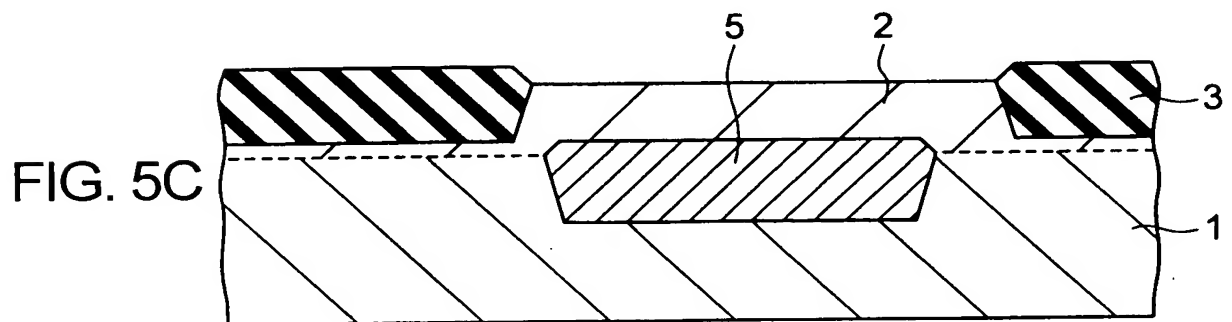
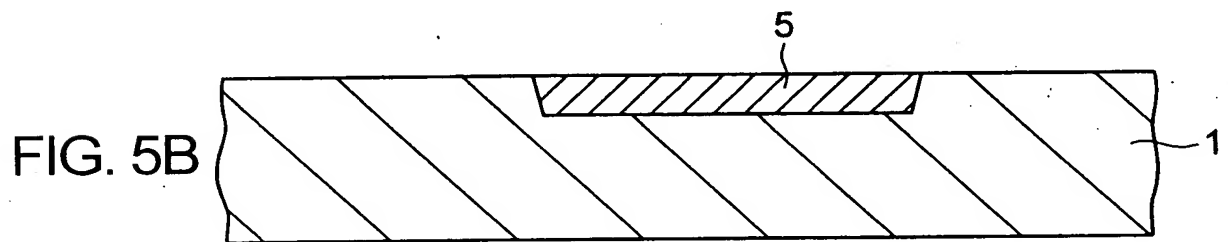


FIG. 6A

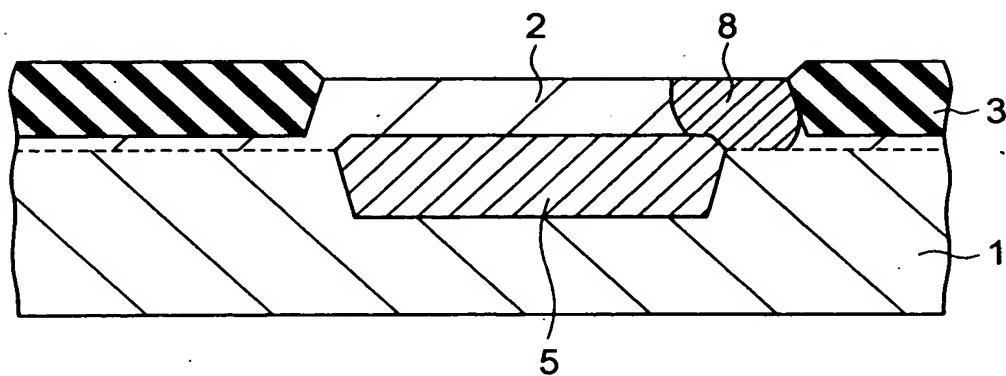


FIG. 6B

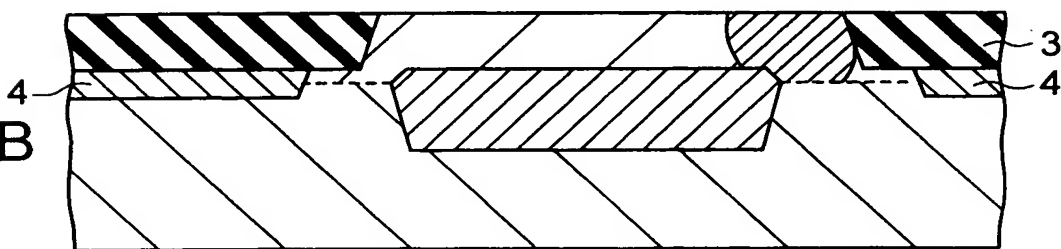
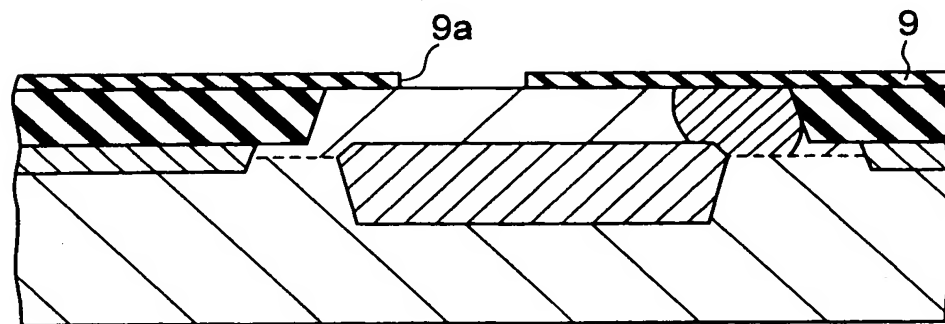


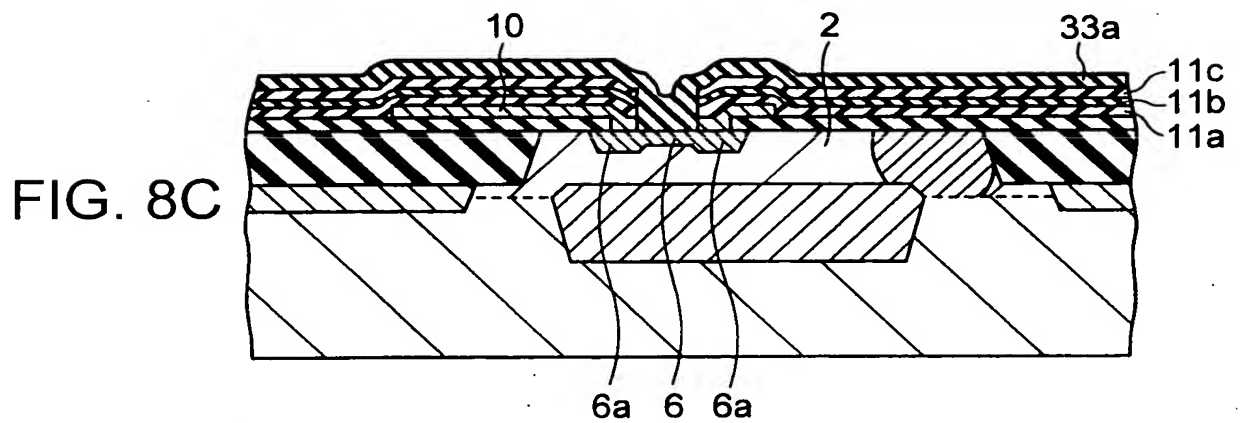
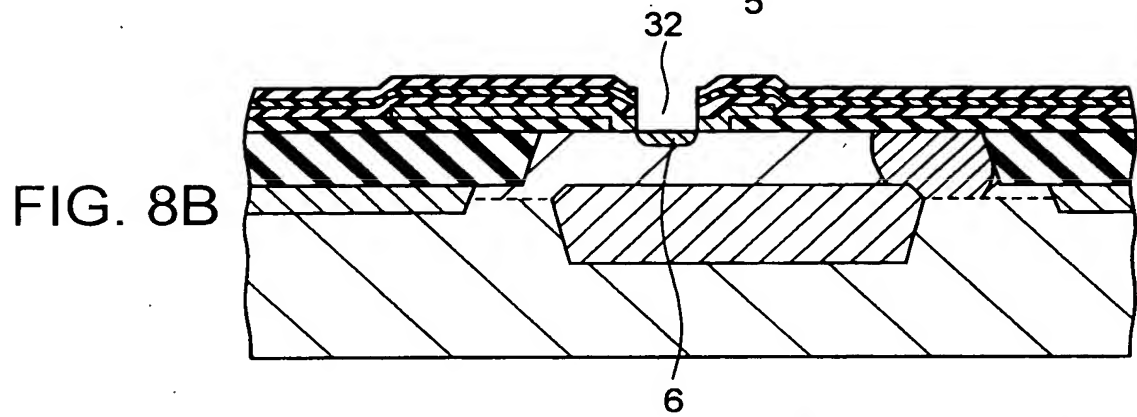
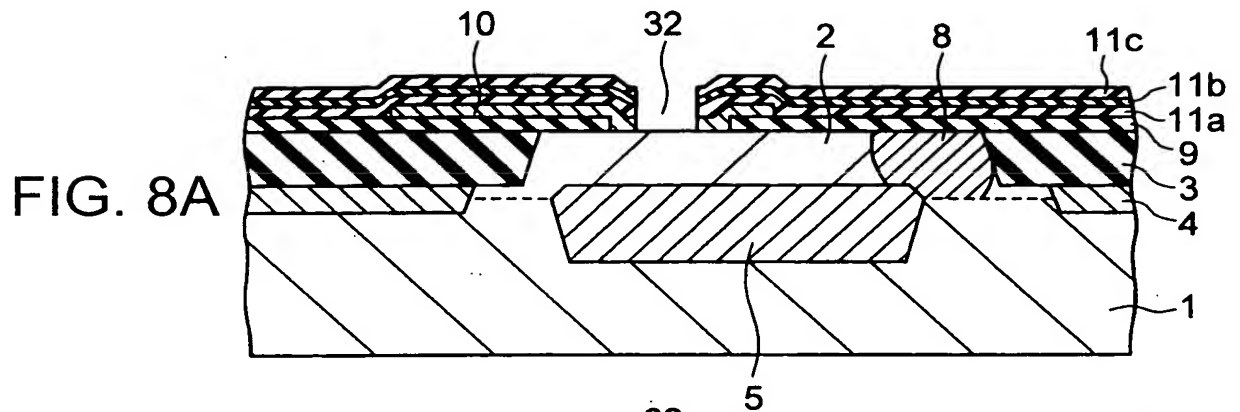
FIG. 6C



[illegible]

A cross-sectional view of a semiconductor device. It shows a top layer with a central protrusion labeled 10. Below this layer is a substrate with a central rectangular region. The top layer has a central protrusion (10) and side regions. The substrate has a central rectangular region and side regions. The top layer is shown in cross-section with diagonal hatching. The substrate is shown in cross-section with diagonal hatching. The central region of the substrate is shown in cross-section with diagonal hatching. The central region of the top layer is shown in cross-section with diagonal hatching. The central region of the top layer is shown in cross-section with diagonal hatching.

A cross-sectional view of a semiconductor device. It shows a substrate 9 with a central region 11a, side regions 11b, and a top layer 11c. The substrate 9 is shown in cross-section with diagonal hatching. The central region 11a is a rectangular block with diagonal hatching. The side regions 11b are rectangular blocks with diagonal hatching, located on either side of the central region 11a. The top layer 11c is a thin layer with a cross-hatched pattern, covering the top of the central region 11a and the side regions 11b.

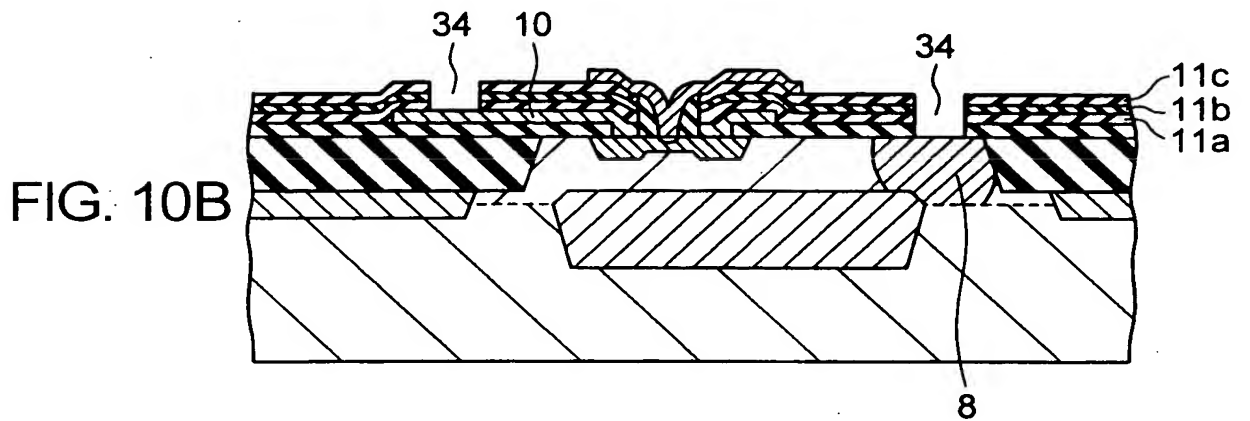
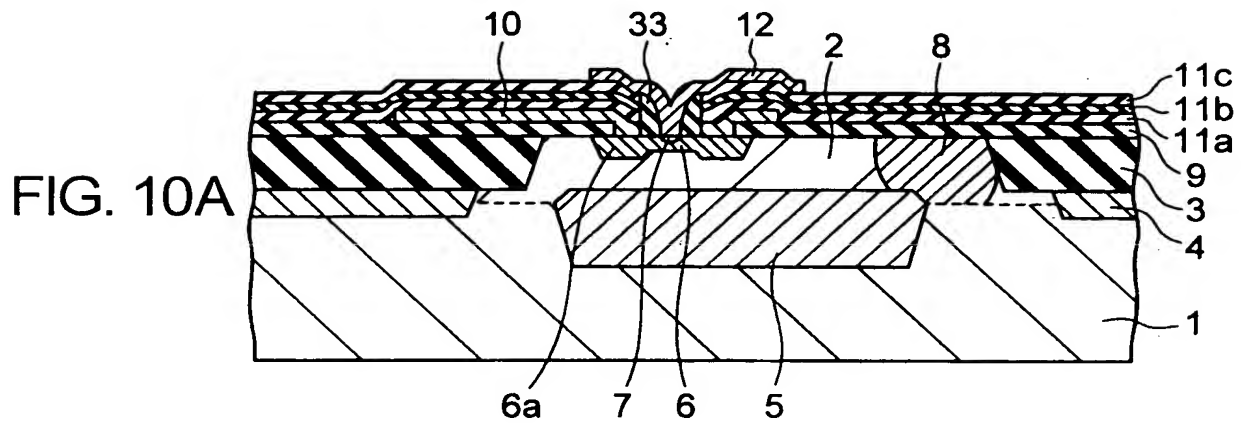




A cross-sectional view of a semiconductor device. A central trench (5) is formed in a substrate (1). A central protrusion (33) is located at the bottom of the trench. The trench is lined with a material (6) and has a top layer (6a). The trench is filled with a material (2). The trench is surrounded by a material (8). The trench is covered by a material (10). The trench is surrounded by a material (11a, 11b, 11c). The trench is surrounded by a material (9). The trench is surrounded by a material (3). The trench is surrounded by a material (4). The trench is surrounded by a material (1).

12a

A cross-sectional view of a semiconductor device. It shows a substrate 7 with a layer 6 on top. Layer 6 has a central opening. Above layer 6 is a top layer 12a, which also has a central opening. The top layer 12a is composed of multiple layers with different hatching patterns.



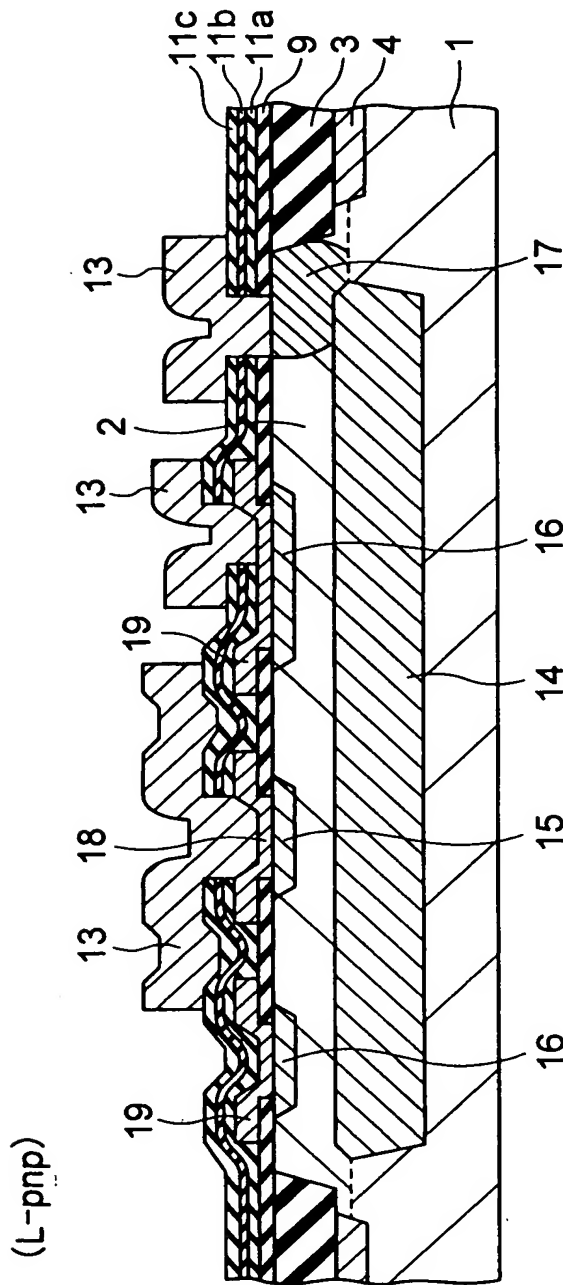


FIG. 11A

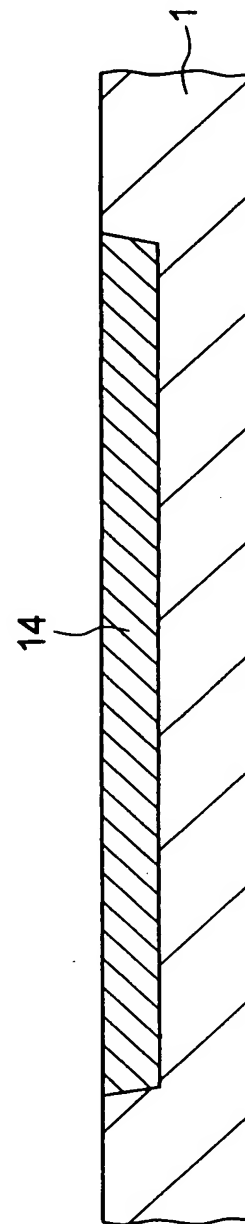


FIG. 11B

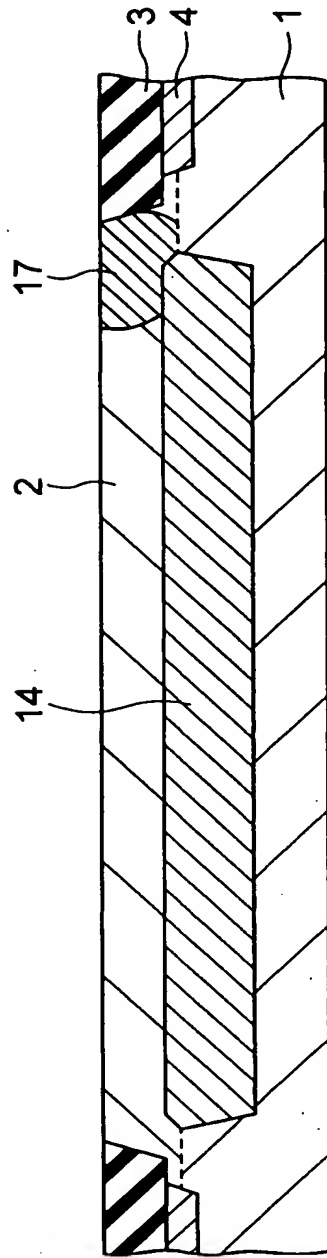


FIG. 12A

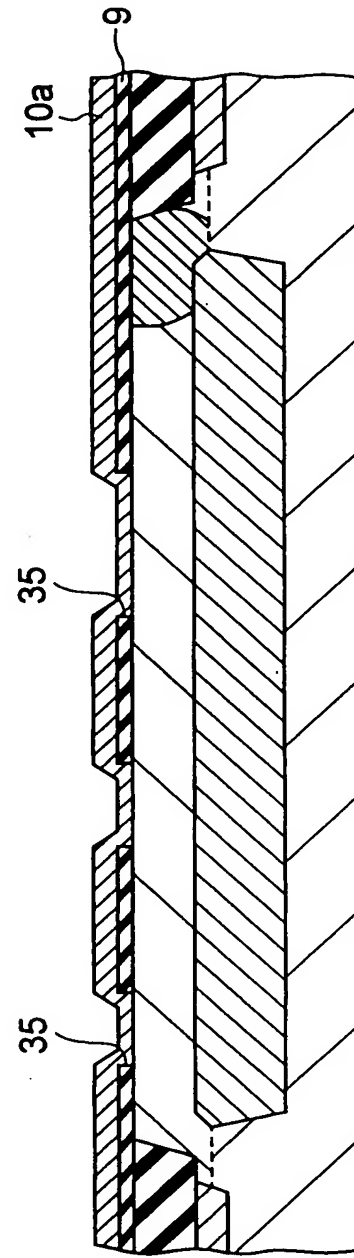


FIG. 12B

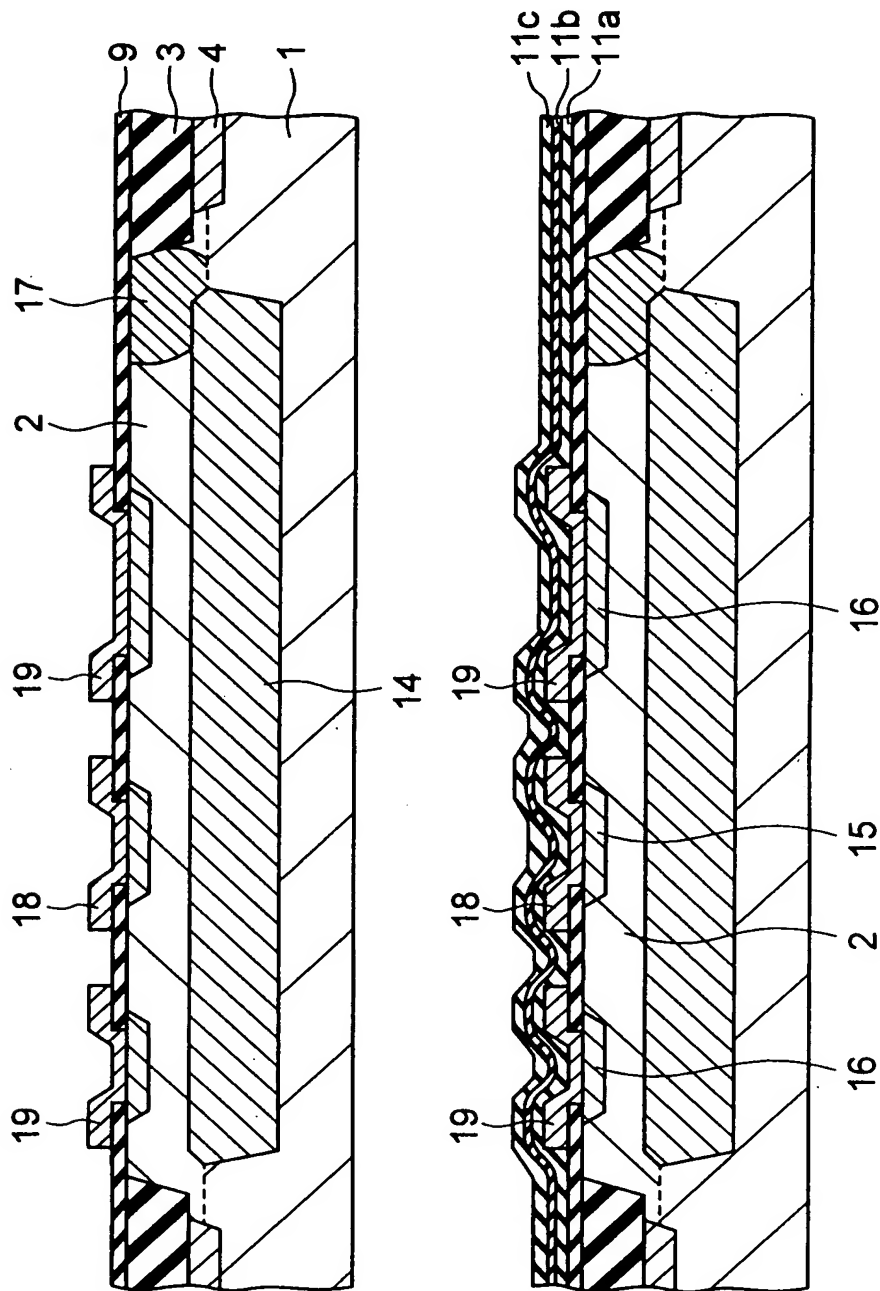


FIG. 13A

FIG. 13B

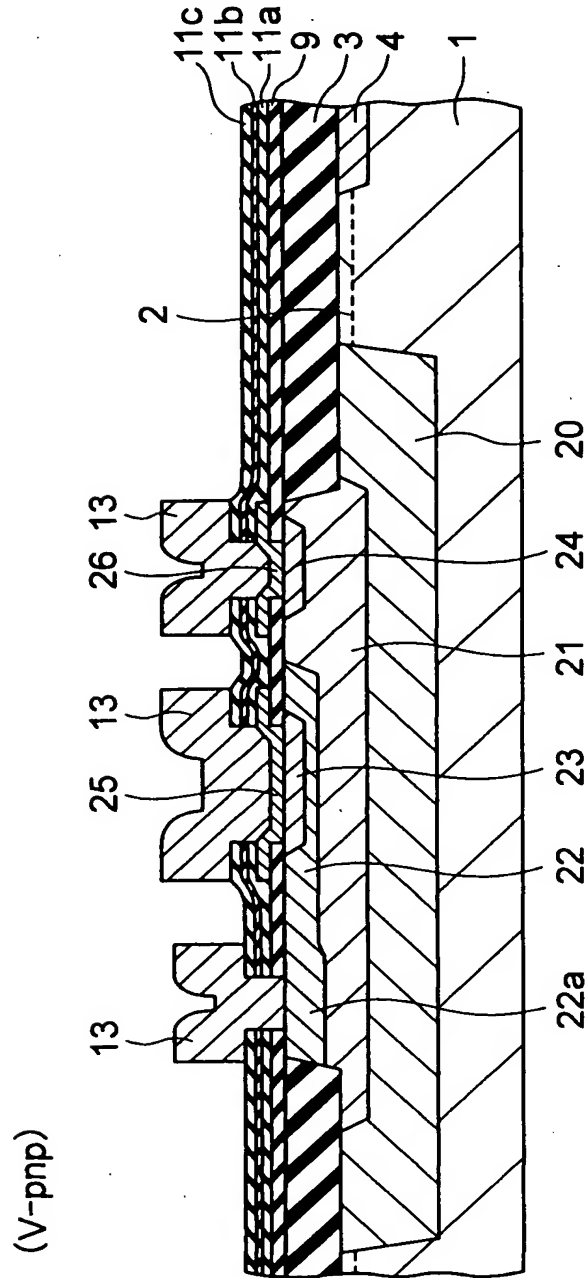


FIG. 14A

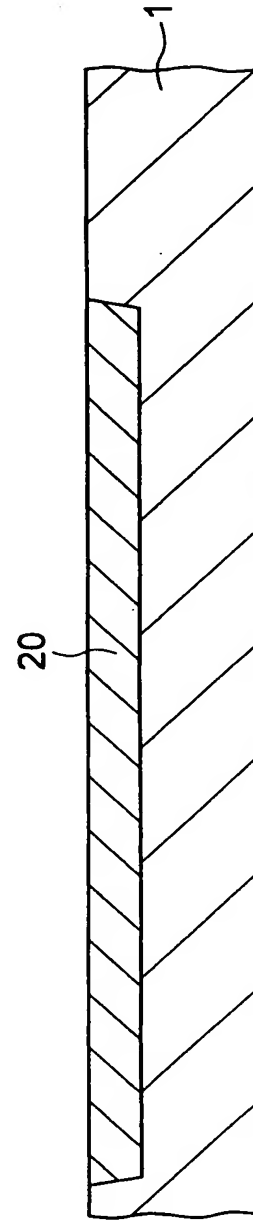
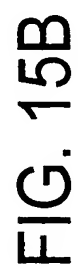
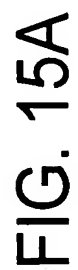
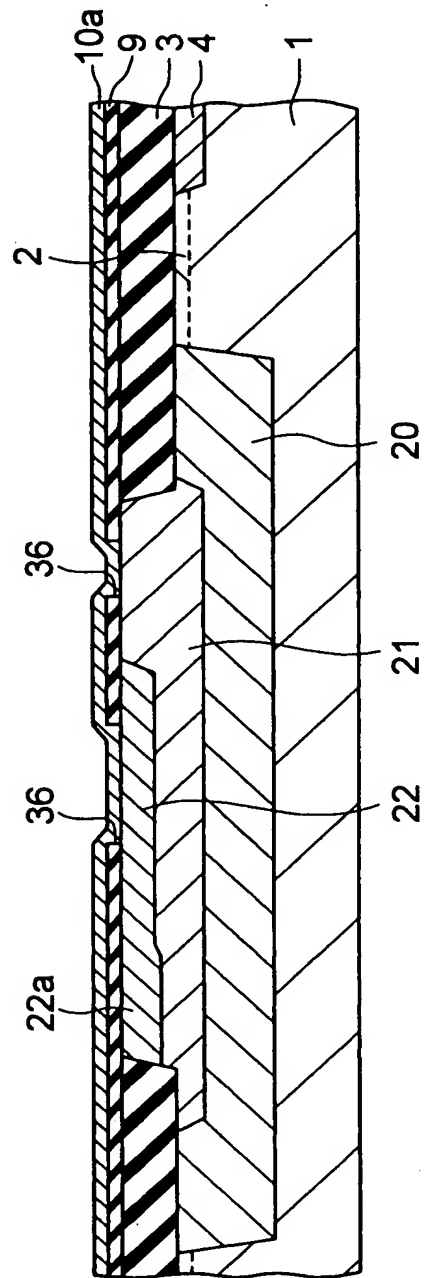
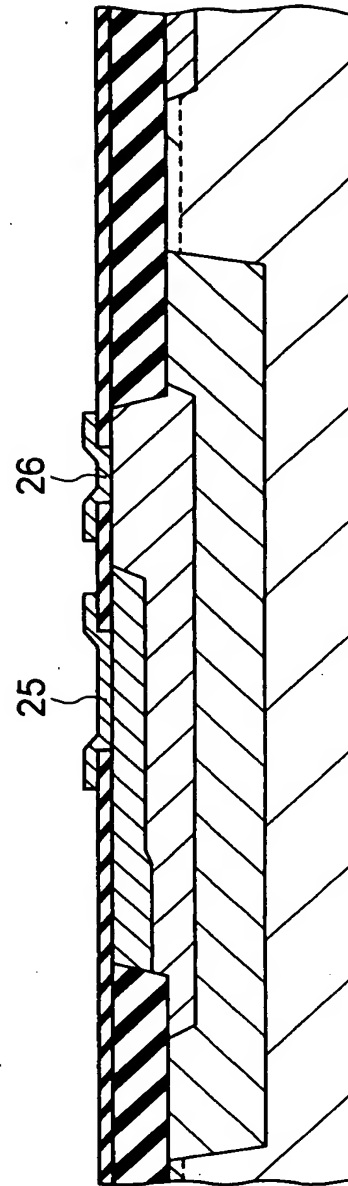


FIG. 14B



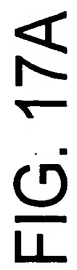


**FIG. 16A**



**FIG. 16B**





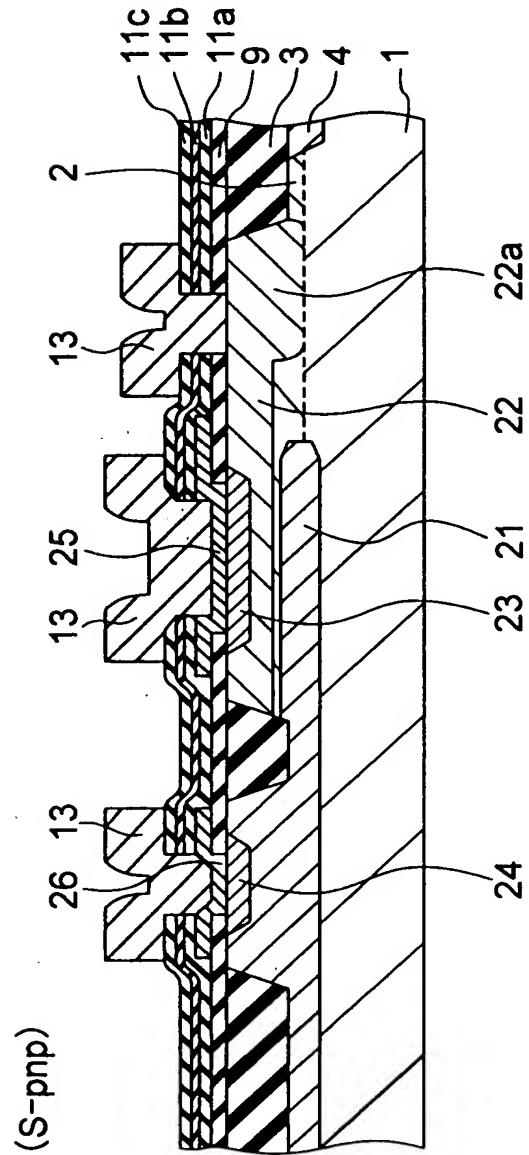


FIG. 18A

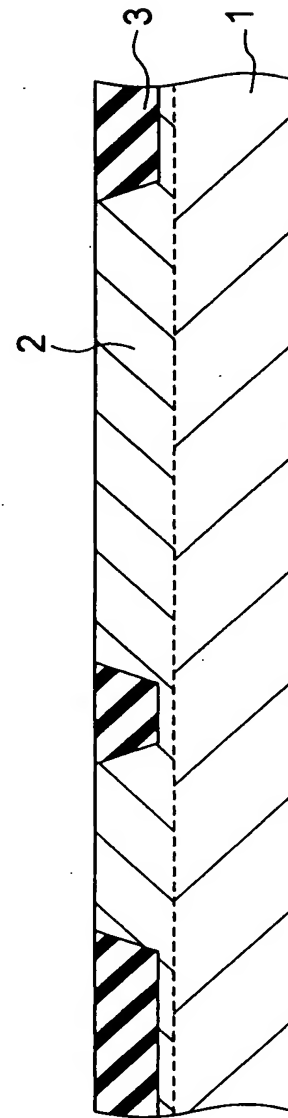


FIG. 18B

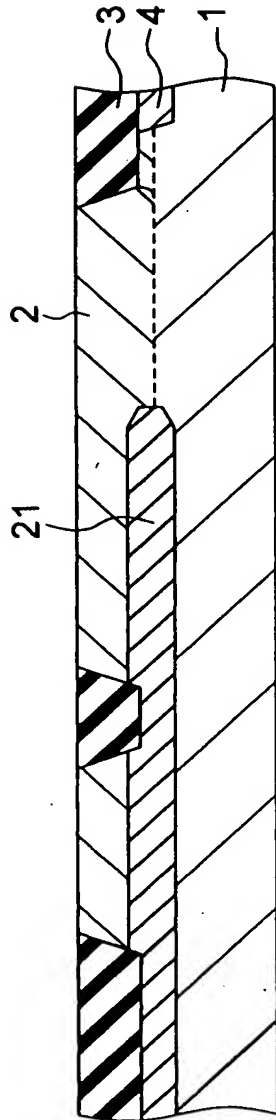


FIG. 19A

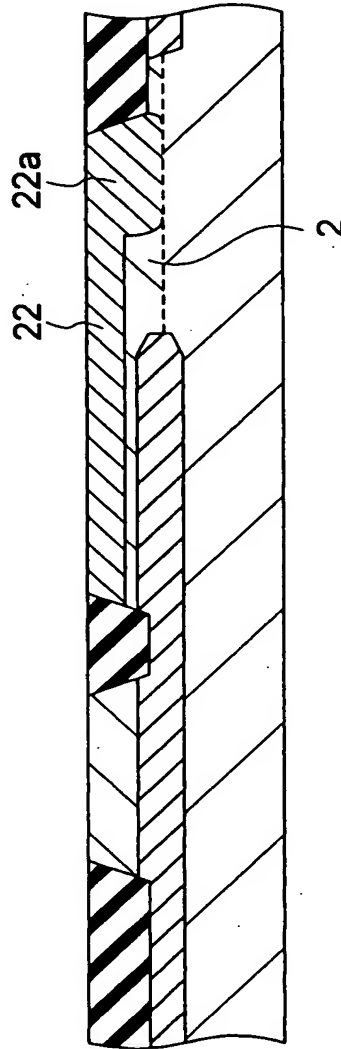


FIG. 19B

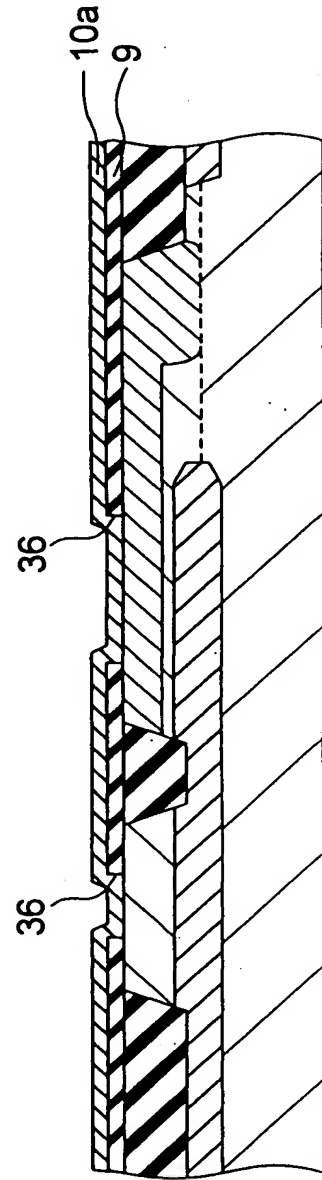


FIG. 19C

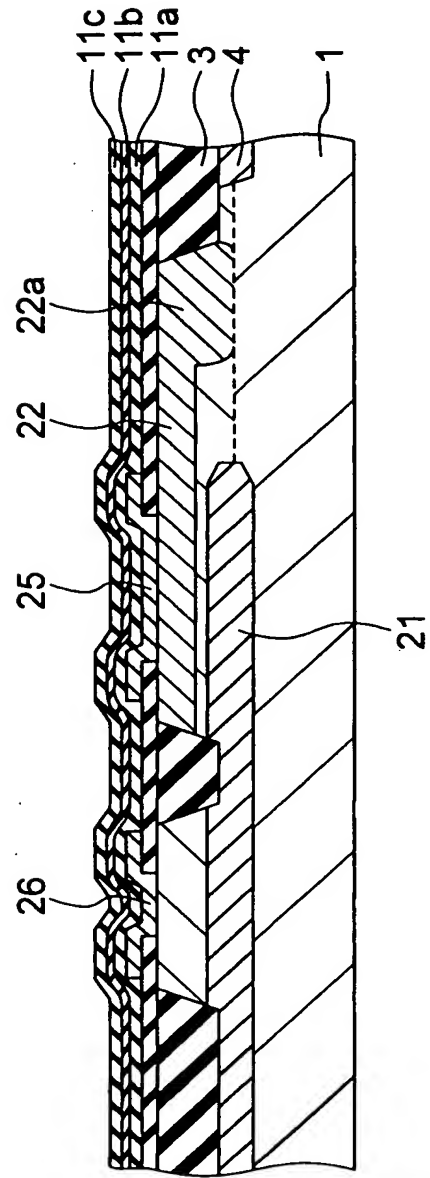


FIG. 20A

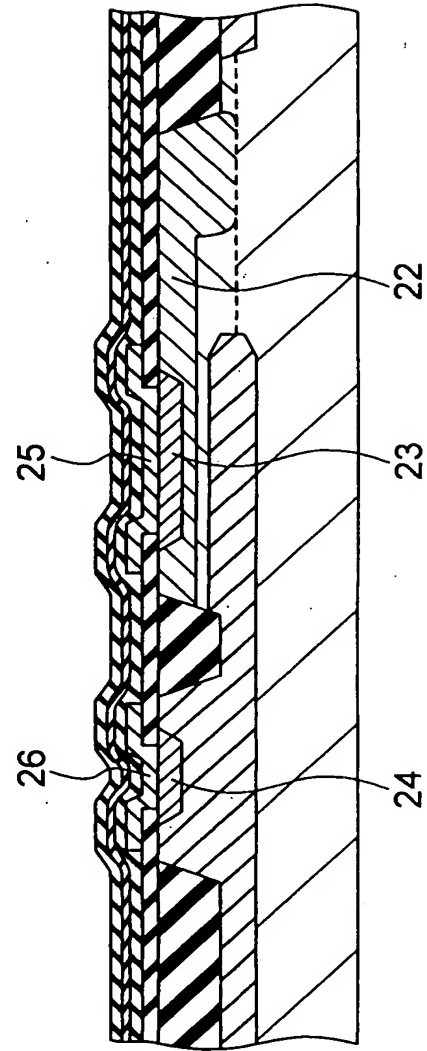


FIG. 20B

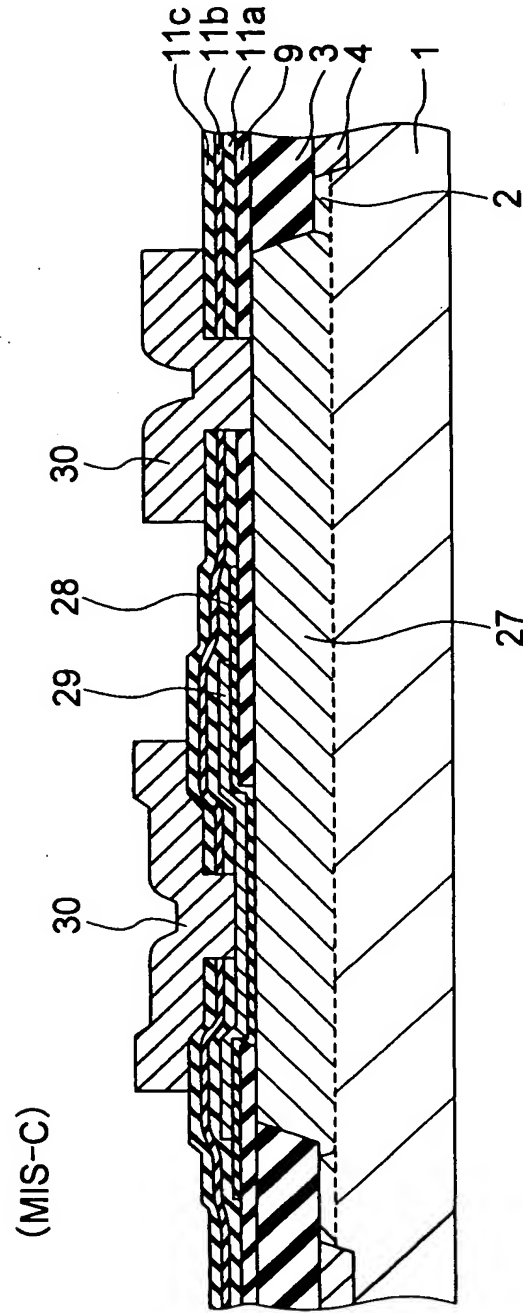


FIG. 21A

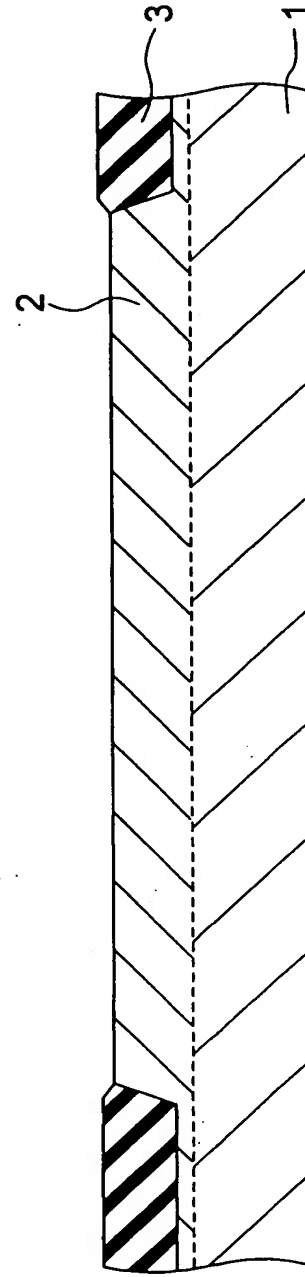


FIG. 21B

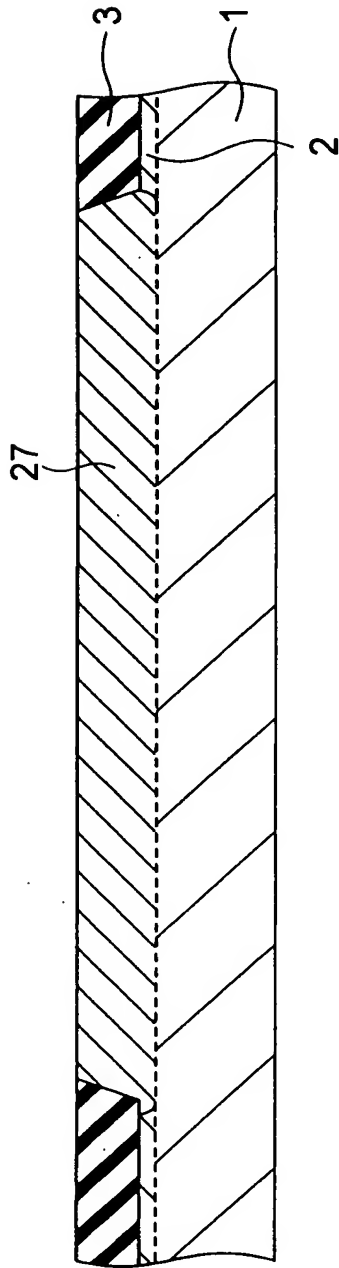


FIG. 22A

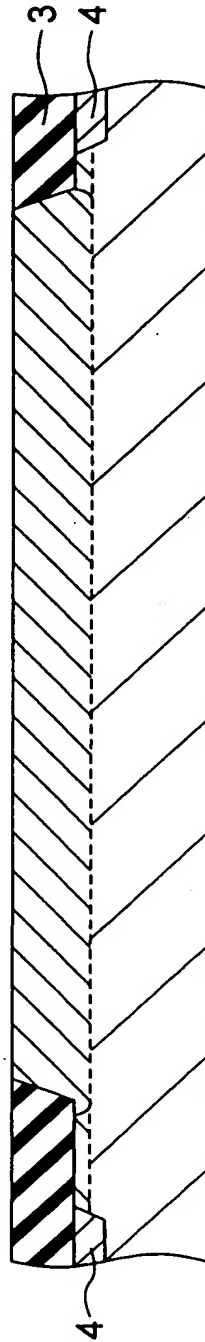


FIG. 22B

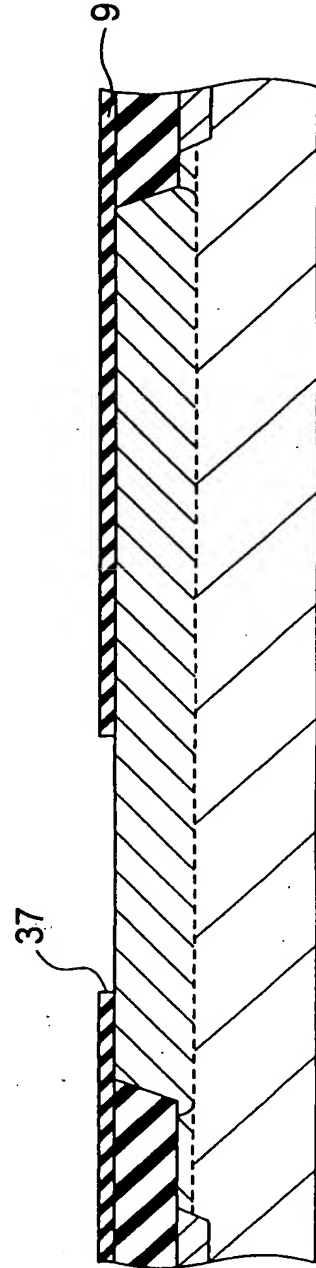


FIG. 22C



